AVR474: ATAVRSB202 Firmware User's Guide

Features

- Provides all needed safety measures for a lithium-ion battery
 - Voltage
 - Current
 - Temperature
- High accuracy voltage and current measurements
- Communication
 - TWI/SMBus 1.1 compatible
- Command set based on Smart Battery specification
- HMAC-SHA2 authentication

1 Introduction

This document describes an example Smart Battery implementation using the Atmel[®] ATAVRSB202 evaluation kit. The implementation demonstrates how to use the Atmel ATmega16HVB/32HVB to gain optimal safety and measurement accuracy for a lithium-ion rechargeable battery pack. All code is available under a limited license agreement to allow for easy evaluation and further development.

The SB202 targets smart batteries with two, three, or four lithium-ion and lithiumpolymer cells in series. The product is based on the same firmware source code, but compiled differently for each configuration. The SB202 hardware for evaluation of the ATmega16HVB/32HVB device and the SB202 executable file are available as the Atmel ATAVRSB202 evaluation kit.

Figure 1-1. Atmel SB202 evaluation kit hardware.







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Application Note

Rev. 8237A-AVR-03/11



2 Overview

The main purpose of a Smart Battery implementation is to protect the battery from overcharging, over-discharging, and use outside its temperature and current limits. It also estimates the battery's remaining capacity, and communicates this to a host/application.

Often, smart batteries offer a method for authenticating the battery. The authentication makes it possible to ensure that only a compatible battery is used for an application. This allows the manufacturer of the application to guarantee that the application will work as intended with regard to battery lifetime and safety.

The Atmel ATmega16HVB/32HVB has dedicated autonomous hardware to protect against short circuit and excessive currents in both directions. Other safety conditions, such as cell voltage level and operating temperature, are handled by the CPU. To ensure good performance, the coulomb-counter ADC and the voltage ADC (CCADC and VADC) are used to gather accurate information about the operating conditions of the battery. The CPU/firmware collects and processes this information, and responds accordingly. The dedicated and specialized hardware modules are described in the datasheet, and this application note demonstrates how they can be used to their best.

The CCADC can be set to trigger an interrupt at fixed intervals, and operates in power-save mode. For this reason it is used as a timebase in this implementation. The CCADC accumulates (averages) the current for one second, and every time a conversion is completed, the main loop will run one loop and the ATmega16HVB/32HVB will go back to sleep. How deep it can sleep depends on whether all modules started in the main loop are finished or not, and whether or not there is ongoing communication.

A hardware TWI module is used for communication. All transmissions have to be initiated by the host/application, but the battery can answer.

The Atmel SB202 is designed for 2s, 3s, and 4s applications. The #define "BATTPARAM_CELLS_IN_SERIES" in the header file determines whether the code should target the 2s, 3s, or 4s configuration. The hardware must be configured for use with different cell counts. This is described in the hardware user's guide.





3 Battery safety

Making sure the battery is not a safety risk for the user is the most important task for the Atmel ATmega16HVB/32HVB. A lithium-ion battery can become very hot and even explode if overcharged or if too much current is drawn from it, and so good protection is needed for a commercial battery.





3.1 Battery protection hardware module

The hardware battery protection on the Atmel ATmega16HVB/32HVB disables both FETs when too much current flows in or out of the battery. It has three limits for discharging and two for charging. The limits can be set to different currents and reaction times. This allows a very fast short-circuit detection, but allows for lower charge/discharge spikes without cutting supply to the host/application. Table 3-1 shows an example of how the three discharge limits can be set up.

Table 3-1. Example timings for battery	protection.
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Current exceeds	Duration for discharge FET to be disabled
2A	20ms
3A	2ms
6A	125µs

In this implementation, the lowest discharge current limit (called discharge highcurrent protection) is disabled to allow faster discharges during testing. The parameters are stored in the EEPROM and used to configure the module at startup.

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Multiple charge over-/high-current protections in a row indicate a malfunctioning charger. In that case, the charge FET is disabled and will not be enabled again until a discharge current higher than standby is detected. That way, the battery is protected even if disconnected from the charger and connected again.

3.2 Firmware-based battery protection

The firmware-based battery monitoring of the operating conditions is protecting the battery from over-voltage, under-voltage, and hazardous temperatures.

3.2.1 Current

Because the battery lifetime is decreased by high charge and discharge currents, the current flowing in/out of batteries should be limited to a reasonable level, which can be determined according to the battery characteristics data and a realistic application scenario. It might also be desired to use more sophisticated current limitation schemes/algorithms than simple thresholds. This is left up to the end user to implement.

3.2.2 Temperature

Very high or very low operating temperatures reduce the lifetime of the battery, and moreover, high temperature can also be a sign that the battery is damaged. Therefore, it is common practice to disable charging/discharging when the temperature is outside a certain temperature range. This is a good idea both for general safety and battery lifetime. This implementation checks the temperatures every four seconds (to minimize active time and power consumption). This is considered sufficient for most batteries, as rapid thermal changes are not expected.

By default, cell temperature monitoring is disabled because no thermistor is soldered on the Atmel SB202 at assembly. Thermistors are, however, provided with the SB202 kit. See Section 11.3 for more information. Instead, the internal Atmel ATmega16HVB/32HVB temperature reference is assumed to be the same as the cell temperature.

If the temperature is too high or too low, either the charge or discharge FET will be disabled, depending on in which direction the current is flowing. It will not be enabled again until the temperature is within the allowed limits.

If the internal temperature of the ATmega16HVB/32HVB is outside the operating limits (-20°C to 80°C), the ATmega16HVB/32HVB will turn itself off and the FETs will automatically be disabled.

All the temperature limits for the battery are stored in the EEPROM.

3.2.3 Voltage

By checking the voltage, the battery can protect itself from overcharging and overdischarging. Both of these conditions reduce the battery lifetime and are a safety risk. Therefore, when a charge current is flowing, the cells are continuously checked for over-voltage, and similarly, while discharging, they are checked for under-voltage.

When the voltage is too high, the charge FET will be disabled. It will not be enabled again until a discharge current higher than standby is flowing. The protection works the same for the discharge FET; after an under-voltage condition, the discharge FET will not be enabled again until a charge current is detected.





When the discharge FET is disabled, its body diode is conducting in the charge direction. However, the diode causes a voltage drop that reduces the voltage difference between the charger and the battery stack, which again causes a reduced charging current. If the battery voltage is high (~3.55V and up), virtually no charge current will flow when the charger is charging with a standard 4.2V.

This condition can occur if the cell voltage drops below the low-voltage limit due to high current drawn from the battery (for example, 3C). In this case, the remaining capacity of the battery is still fairly high. When the discharge FET is disabled by hitting the low-voltage limit, the battery cell will recover and the voltage will increase. The voltage can increase from 2.7V to 3.6V, which is high enough to limit the charging.

To handle this scenario, the discharge FET is enabled if the battery voltage is above a given threshold or if a charging current is detected (a few mA is enough).

If the voltage drops very low (for example, 0.2V below minimum operating voltage for the cell), the Atmel ATmega16HVB/32HVB turns itself off to limit further discharging of the battery. To avoid shutting down on short discharge spikes such as due to high outrush current when inserting the battery in an application, for example, the voltage has to be low for two seconds before power-off is performed.

The voltage is also used for:

- Checking whether cell balancing should be activated or not on the Atmel SB202
- Check when the battery is fully charged or discharged; useful for gas gauging modules
- Disabling deep under-voltage recovery (DUVR) mode. When the voltage is high enough, DUVR mode is disabled, and the firmware can control the FETs

All limits for the voltage protection are stored in the EEPROM.

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4 Battery parameters/settings

Most battery parameters are stored in the EEPROM for easy reconfiguration. Those values are in "physical" units; that is, mA, minutes, etc. Internally the Atmel SB202 uses other units to reduce computation complexity to a minimum. Therefore, at startup, some parameters in the EEPROM are converted into other units and stored in the SRAM.

Changes to some settings that require that the code be recompiled affect more than just a value in the EEPROM. Most obvious are settings for the number of cells and the availability of external temperature sensors.

All parameters and settings are located and commented in the battery_pack_parameters.h/c files. Battery characteristics data are stored in the firmware module that uses them; for example, cc_gas_gauging and voltage_based_SoC.





5 Clocks and calibration

The Atmel ATmega16HVB/32HVB's internal fast RC oscillator is used as the system clock. It runs at a nominal frequency of 8MHz, but the system clock prescaler should be fused to 1/8 for the SB202, resulting in a system clock with a frequency of 1MHz.

The fast RC oscillator varies over temperature. However, this can be avoided by calibrating the fast RC at runtime with the use of the slow RC oscillator, whose frequency can be determined as a linear function of temperature. This makes it possible to calibrate the fast RC oscillator with sufficient accuracy to have reliable UART communication. The calibration is run every time the chip temperature has changed by 2°C.

When the slow RC period is known (calculated), it is known how many fast RC ticks should occur during that period for it to be running at 1MHz. When calibrating, the number of fast RC ticks during eight slow RC periods is counted, and the calibration register is adjusted until the number is as correct as the adjustment allows for. The calibration register is only adjusted one step at a time to avoid changing the frequency too much.

5.1 Real-time counter

There is no need for an accurate real-time counter (RTC) on the Atmel SB202. Realtime is only used for knowing approximately when a number of minutes have passed, and is not used for any calculations.

The RTC is clocked by the ULP RC oscillator through the CCADC conversion time. Since the actual ULP RC period can be calculated through slow RC, it is possible to improve the accuracy of the RTC if needed.

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6 Initialization flow (after reset)

During initialization, all peripheral and firmware modules are configured, calibrated, and prepared for operation. Upon the very first startup (that is, power-up after programming), CCADC offset adjustment is also performed. The initialization sequence is listed below.

- 1. Set up the watchdog, and check if too many watchdog resets have occurred. If it has, it indicates a major problem, and the battery should be disabled. (Nothing is done in this implementation.)
- 2. Disable unused peripherals and pins to reduce the power consumption.
- 3. Check that the battery parameters and signature row is correct (CRC16). If they are not, the part can be measuring wrong values and have wrong limits for battery protection. So, the battery should be disabled if the checks fail. (Nothing is done in this implementation.)
- 4. Calibrate the bandgap. If it fails, the readings from the ADC modules cannot be trusted, and, therefore, the battery will be disabled.
- 5. Initialize the hardware battery protection module.
- 6. Set up the VADC module with gain coefficients and offsets from the signature row.
- 7. Values to convert between internal units from the CCADC to mA/mAh are calculated from the shunt resistor value stored in the EEPROM.
- 8. Some frequently used limits from the battery parameters are converted to internal units to avoid doing that calculation every second.
- 9. The VADC runs one scan of all available inputs to have values for the first main loop and also to check if the DUVR mode can be disabled.
- 10. If a serious failure has not occurred earlier in the initialization process, the CCADC and coulomb counter gas gauging modules are configured. The remaining capacity for the CC-based gas gauging is set by using the state of charge (SoC) from the voltage-based gas gauging. It is, however, marked as inaccurate and updated as soon as the voltage-based gas gauging has an accurate estimation.
- 11. If it is the very first start-up, it will measure the CCADC offset. This process takes up to 30 seconds.
- 12. Finally, the communication is initialized and global interrupts enabled before entering the main loop.





7 Main loop

The purpose of the main loop is to gather and react to data from the interrupts. It runs through all available data and checks that all are within the limits. If errors are discovered during charging or discharging, the corresponding FET is disabled and an error flag is set. If no error flags are set at the end of the main loop, the FETs will be enabled again. Because the main loop is run once per second, the FETs will be disabled for a minimum of one second when the firmware detects an error.

Figure 7-1. Simplified flowchart for the main loop.



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The hardware battery protection module prevents the FETs from being enabled within one second after a battery protection event (caused by too high current) has been triggered. Because the current protection is handled by hardware, the main loop doesn't have to check for that before enabling the FETs.





8 Interrupts

The implementation is interrupt-based: All processing is based on interrupt triggers, and interrupts (and flags) are an essential part of the implementation. The interrupts used in the implementation are listed in Table 8-1.

Table 8-1. Interrupts used in the Atmel SB202 Smart Battery application.

Interrupt source/function name	Description
Voltage regulator monitor interrupt VREGMON_ISR()	Stores all interrupt settings for the various modules and enters power- save until the voltage regulator is okay again or CREG is empty. If the voltage regulator is okay, restores the interrupts and continues operation. See the Atmel ATmega16HVB/32HVB datasheet for a description of how the voltage regulator monitor works
Watchdog timeout interrupt WDT_Timeout_ISR ()	Only used by the voltage regulator monitor interrupt to wake the device up and check if the voltage regulator is okay
Timer 0 output compare match interrupt RCCAL_InputCapture_ISR()	Captures the number of fast RC clocks during one slow RC period. See Chapter 5, Clocks and calibration, on page 8
Battery protection interrupt BATTPROT_BatteryProtection_ISR()	Triggered when the hardware battery protection module disables the FETs due to excessive currents or short circuit. Sets a flag, which is used to alert the host. If it was an overcharge, it increases the number of times this has happened to be able to detect a malfunctioning charger.
CCADC accumulating conversion complete interrupt Ccadc_Acc_ISR()	If the CCADC is set to negative polarity, the result is negated; otherwise it is just stored as is. The main loop will then process the result. If polarity switching compensation (see Section 10.2) is activated, the compensation is done here.
Voltage ADC conversion complete interrupt VADC_ISR()	Flags that a channel or group of channels is complete. The main loop will then process the result. If there are more channels to scan in the ongoing sweep, sets the MUX and starts the VADC again. Otherwise turns the VADC off.
TWI (SMBus) interrupt request	Maintains the TWI (SMBus) state machine to implement the communication
Timer 1 overflow interrupt T10VF_ISR()	Provides timer tick for the code. The timeout period is 2.048ms
Timer 1 output compare match B interrupt T1_COMPB_ISR()	Checks the hold time of the button pushed. After the hold time is larger than the predefined period, the LED will be lit to indicate the volume of capacity or the error code. The LED on time is set at LED_ON_TIMEOUT
Timer 1 output compare match A interrupt T1CMPA_ISR()	Reduces the LED on time until it is zero, and then turn off the LEDs
Pin change interrupt 0 PCINT0_ISR	Checks the button input, and will trigger if there is a pin change on the button. This enables the timers to show status codes on the LEDs

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9 FET control

If an error occurs that requires the current flow to be cut, the FET will get disabled immediately and an error flag will be set. The FET will not be enabled again until all errors have disappeared; that is, all error flags are cleared.

The flags are divided into different variables in the code, but only the flag name is used here.

> connected) is too low. Will disable either the charge or discharge FET when set, depending on which direction the current is flowing. Will prevent both FETs from being enabled

Clearing conditions Description Flag name CriticalConditonDetected Will never get cleared Set if the bandgap or VADC can't be calibrated/initialized, and will keep both FETs disabled all the time ChecksumFailure Will never get cleared Set if either the signature or EEPROM battery parameters CRC is wrong. Is not done in this implementation, but the battery should be disabled if the checksums are wrong InDUVR Cleared when DUVR mode is Set at start-up and if the code detects that the DUVR mode disabled has been enabled again. Will prevent both FETs from being enabled, but the DUVR has control over the charge FET so charging is possible SystemIsInStandby Cleared if the current is higher Set if the current is less than the active current threshold. By than the active current threshold default, that is 10mA in either direction ReoccuringChargeProtection Cleared when an active discharge Set if a too-high charge current is detected too many times in a current is detected row, which indicates a malfunctioning charger. Will disable the charge FET when set and prevent it from being enabled again until cleared ChargingProhibited Cleared when an active discharge Set if a too-high voltage is detected. Will prevent the charge current is detected FET from being enabled while set DischargingProhibited Cleared when an active charge Set if a too-low voltage is detected. Will prevent the discharge current is detected FET from being enabled while set VoltageTooHigh Cleared if the last voltage was Set if the last voltage was too high for any cell. Disables the below the maximum for all cells charge FET VoltageTooLow Cleared if the last voltage was Set if the last voltage was too low for any cell. Disables the above the minimum for all cells discharge FET CellTemperatureTooHigh Cleared if the last temperature Set if any cell temperature (or the internal temperature reading is below the maximum reference of the Atmel ATmega16HVB/32HVB if no thermistor is connected) is too high. Will disable either the charge or limit discharge FET when set, depending on which direction the current is flowing. Will prevent both FETs from being enabled while set CellTemperatureTooLow Cleared if the last temperature Set if any cell temperature (or the internal temperature reference of the ATmega16HVB/32HVB if no thermistor is reading is above the minimum

Table 9-1. FET control conditions.



while set

limit



10 CCADC

The result from the CCADC is used to check the current level, compute the average current over one minute (approximated to save memory), and compute the accumulate charge that has flowed in and out of the battery. Only the accumulated result from the CCADC is used when checking limits and accumulating charge. The CCADC is set to a one-second conversion time and to trigger an interrupt when conversion is complete. That way it can also be used to update the RTC. The actual timing will depend on the temperature, but as described in Chapter 5, Clocks and calibration, page 8, the RTC does not need to be very accurate.

The actual conversion time is important when accumulating current for counting the charge that has flowed through the battery. The CCADC is clocked by the slow RC oscillator, and its period can be calculated from the internal temperature reference of the Atmel ATmega16HVB/32HVB and the slow RC temperature predication value that is stored in the signature row. The cc_gas_gauging module is responsible for accumulating the capacity and compensates for the actual slow RC period.

If polarity switching is enabled, the CCADC accumulating conversion complete interrupt is responsible for storing the result so that it is always positive for a charging current and negative for a discharging current.

When a new current result is ready from the CCADC, it is passed to the battery_current_monitoring module by the main loop, where it is added to the oneminute average current. The average is calculated as shown in Equation 10-1. **Method for calculating average current.** The scaling is used to improve accuracy and is removed when the average is returned.

NOTE An exponential filter is used to estimate a one-minute moving average current. This is done to save memory, as a one-minute moving average is very SRAM-consuming.

Battery_current_monitoring also gives easy access to the current and offset calibrated current for other modules that need it.

Equation 10-1. Method for calculating average current.

 $New average = \frac{124 * Old \ average + 4 * current * 2^{n}}{128}$ $n = AVERAGE_CURRENT_SCALING \ (default \ value: 4)$

10.1 CCADC offset

The CCADC has a certain offset. When accumulating charge, it can be cancelled out by switching polarity at a fixed interval. But as it is possible to measure the offset, it's nice to use that to correct the measurement when it's used as momentary current. It helps the most on low current when checking whether the battery is in standby mode or not.

The offset is measured the first time the battery is started and takes 20-30 seconds, during which both FETs will be disabled. It discards the first sample after every switch and compares the average of the other samples between positive and negative CCADC polarity. Half the difference is the offset, and that can then be added or removed (depending on polarity setting) to later measurements to get a more correct value.

Switching polarity too often is not a good idea because the first accumulating conversion after a polarity switch is not correct.

10.2 Challenges with polarity switching

The ACC conversion from the CCADC is calculated from the average of 256 instantaneous conversions by hardware (one-second conversion time). But every time the polarity is switched, the first two to three instantaneous current conversions are wrong. The first one is completely off, the second quite wrong and the third is almost always correct, and if not, then only slightly wrong.

Figure 10-1. Example ICC samples before and after a polarity switch.



This is caused by settling time in the CCADC, which requires two to three ICC conversions to settle. In the example in Figure 10-1, the error for a one-second conversion time and a constant current of -185 would be:

$$error = \frac{254*185 + (-140+101) - (256*185)}{256*185}\% = -0.86\%$$

To remove the problem as much as possible, the two or three samples after the switch should be removed from the ACC result for that second and replaced with an average of the ICCs before and after them.

To do that, the part has to wake up three or four extra times after a polarity switch to read the ICC results, and that adds active time and, therefore, power consumption. It also adds complexity and code space.

The Atmel SB202 takes a simpler approach that still removes most of the error. The sum of the two samples after the switch is small compared to one ICC sample, so they are already considered "removed." And instead of adding the average of the ICC readings around them, only the ICC sample from just before the polarity switch is used. As that sample is available when switching the polarity, practically no runtime is added.

With the same assumptions as in last error calculation, the error will now be:

$$error = \frac{(254*185+(-140+101)+2*182)-256*185}{256*185}\% = 0.095\%$$

NOTE

In Figure 10-1, the results are not polarity compensated, so the result from before the switch is negated before using it in the error calculation.

Since the ACC result has the same range for different conversion times, the result is downscaled by the hardware. Therefore, the ICC result also has to be downscaled before it is added to the ACC result.

For different values of samples and downscale from Table 10-1, the ACC result is:

$$ACC = \begin{pmatrix} samples \\ \sum ICC[n] \\ n = 1 \end{pmatrix} >> downscale$$



Table 10-1. ICC samples for different ACC conversion times.

Conversion time	Samples	Downscale
1s	256	3
500ms	128	2
250ms	64	1
125ms	32	0

To replace the two "missing" ICC samples, the ICC sample from just before the switch has to be divided by four (doubled and then scaled down three bits) before adding it to the ACC result.

10.3 Shunt calibration

The result from the CCADC is the voltage drop over the external shunt resistor, which on the Atmel SB202 has a value of $5m\Omega$, $\pm 1\%$. The shunt resistance is used with the result from the CCADC to calculate the current. As a calibration option, the shunt value can be changed at runtime by sending a new shunt resistance value via the communication interface.

An ammeter can be used to measure the exact current flowing in/out of the batteries. This information can then be used to calculate what the shunt resistance really is. This is described in more detail in the Atmel AVR491 application note.

The shunt resistance can be set between $4000\mu\Omega$ and $16000\mu\Omega$ using the ShuntCalibration command (0x2A). Other values are possible, but require changes to the code to avoid computational overflows.

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11 VADC

The Atmel ATmega16HVB/32HVB MCU has a five-channel VADC for measuring cell voltage, chip temperature, and cell/battery temperature. The chip temperature uses an internal diode. External thermistors are required to measure the battery cell temperatures.

Immediately after a CCADC ACC result is ready, a new VADC scan is configured and started. This is to ensure that the data are ready when the main loop can process them (because the VADC conversion takes a long time compared to the processing of the data). Ideally, the VADC should only run while the CPU is busy processing information. Otherwise, energy is wasted in noise-reduction-mode/idle-mode sleep, or even active mode, just waiting for the conversion to complete. In reality, noise-reduction sleep is used whenever it is required to wait for a conversion to complete.

Configuring the VADC scan means to set which channels should be sampled. It depends on how many cells and thermistors are used. The cell voltages are sampled every second, but temperatures are sampled only every fourth second as they do not change that fast. The ADC input channels are scanned in the same order as they are processed in the main loop. This is to ensure that the CPU can process data while converting the next sample.

When one channel is finished, the VADC conversion complete interrupt routine sets a data ready flag to notify the main loop. This allows the main loop to process, for example, the result from cell one voltage while the VADC is sampling cell two voltage. The interrupt routine advances to the next input channel in the scan (reconfigure the VADC mux) or, if the scan is completed, turns off the ADC sample.

11.1 VADC calibration

To ensure optimum accuracy when using the VADC, all results must be corrected for offset and gain error. The offset and gain compensation can be read from the HVB signature row. Please refer to the datasheet for more details.

Equation 11-1. Offset and gain compensation of the VADC result.

 $ADC_{compensated} = (ADC_{result} - ADC_{offset}) \cdot ADC_{gain}$; (downscaled by 2¹⁴)

11.2 Chip temperature

To calculate the chip temperature, the VADC result is multiplied by the VPTAT value from the signature row and scaled down as described in the datasheet. Further, it is multiplied by 10 to get results in 0.1K, as required according to the SBS specification.

All temperatures are stored in 0.1K.

NOTE The VADC result for the internal temperature reference only requires gain compensation. Offset compensation is not required.

11.3 Cell temperature

Because no thermistors (NTC) are soldered on the Atmel SB202 during assembly, cell temperature reading (and processing) is disabled by default. Instead, the chip temperature is assumed to be the same as the cell temperature when evaluating the system temperature.





To use one or two thermistors, connect them as described in the Atmel AVR455 application note and change two defines in battery_pack_parameters.h (search for CELLTEMPERATURE_INPUTS and read the comments just above it).

To convert the VADC result to mV, the result has to be offset calibrated, multiplied with a gain coefficient, and then scaled down. The downscaling is chosen to maximize accuracy so the VADC module by default returns 200*voltage in mV.

Equation 11-2. How to calculate voltage on the VADC according to the datasheet.

$$ADC_{mV} = \frac{1}{10} \cdot \frac{(ADC_{result} - ADC_{offset}) \cdot ADC_{gain}}{16384}$$

Equation 11-3. How the Atmel SB202 calculates the scaled voltage from the VADC result.

$$ADC_{scaled_mV} = \frac{(ADC_{result} - ADC_{offset}) \cdot ADC_{gain}}{8192}$$

The thermistors supplied with the SB202 are Mitsubishi RH16-3h103f, and the NTC firmware module in the ntc_rh163h103f.c file converts the scaled voltage from the VADC module to Kelvin or degrees Celsius. To use another NTC, other data used by the firmware module have to be used.

11.4 Cell voltage

To get the real voltage from the VADC result, an offset has to be added and the result multiplied with a gain coefficient and then scaled down, as written in the datasheet. This conversion between the VADC result and the actual voltage is calculated only once per conversion; later use of the cell voltage thus does not spend time converting the VADC result to volts.

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12 Gas gauging

Gas gauging is estimating how much capacity and runtime is left in the battery. The Atmel ATmega16HVB/32HVB can achieve high accuracy gas gauging by means of its very accurate VADC and CCADC. The great storage capability in flash, SRAM, and EEPROM allows the use of accurate battery models.

The Atmel SB202 uses a combination of voltage- and coulomb-counter-based gas gauging. The voltage-based gas gauge is used to initialize the remaining capacity, which the coulomb counter then will increase/decrease during use.

12.1 Gas gauging strategy on the SB202

At start-up, the voltage-based gas gauging estimates the state of charge (SoC) using an approximation of the internal resistance of the battery. The remaining capacity is calculated from that SoC and from the latest full-charge capacity stored in the EEPROM. This provides a reasonable initial estimate of the SoC and remaining capacity, though it is not as accurate as the estimate will be when the open-circuit voltage (OCV) is measured, or when the battery has been charged to full capacity once. For this reason, a flag is used to indicate that the SoC/remaining capacity is "inaccurate" and that a better estimation should be performed as soon as possible.

The SoC from the voltage-based gas gauging module is considered accurate when the current has been below the standby current limit for 30 minutes or more. (Threshold for standby current is specified in firmware and stored in EEPROM.) The first time this happens after start-up, the remaining capacity is updated and is no longer flagged as inaccurate.

Remaining capacity is updated every second by the coulomb counter, and it is used to calculate all the information the SB202 can provide to the host/application.

Because the end-of-discharge voltage is reached sooner when high currents are drawn from the battery, the calculation of the runtime to empty takes the current level into account. The calculation uses characterization data for the specific battery cell type to determine how the available capacity changes at different current levels compared to when using only a very small current. Ideally, the characteristic data should be updated as the battery gets older, as the battery characteristics change slightly over time, but this is not offered in this application.

12.2 Voltage-based gas gauging

Voltage-based gas gauging works quite well to determine the SoC from the open circuit voltage (OCV, that is, at no or low current). But as soon as "more" current is flowing, the battery's internal resistance effects reduce the terminal voltage. The resistance changes with temperature, SoC, and battery age, which makes it challenging to accurately estimate the SoC from only the OCV.

Two other problems with voltage-based gas gauging are:

- It only gives the state of charge in percents and no indication of the capacity of the battery, which makes it hard to give an accurate runtime for the battery
- When the current stops, the voltage does not immediately return to the OCV. How long it will take depends on the battery, but generally it takes about 30 minutes





However, the combination of OCV-based estimation and coulomb-counting-based estimation provides a good overall estimation that is not very sensitive to temperature, aging, etc.

12.3 Coulomb counter gas gauging

A coulomb counting approach keeps track of how much current is charged into the battery and discharged from it. It is very accurate, even at high currents. The disadvantage of the coulomb-counting-based gas gauging is that it can measure changes only. This means that it does not offer information about the absolute charge level, and, therefore, an initial charge state is also required.

When doing coulomb-counter-based gas gauging, the current charge/remaining capacity has to be estimated using a voltage-based approach at start-up and also possibly after a long time in standby. If the initial voltage-based SoC estimate is wrong, the coulomb-counter-based estimate will also be wrong. It can, however, calibrate itself when reaching a fully discharged and fully charged state.

By using a coulomb counter, the full charge capacity can be updated as the battery gets older with the following method:

It is known when the battery is fully charged and fully discharged, so how much charge has been used between these states is the full-charge capacity. A full charge on a lithium-ion cell is reached when the charge current has dropped low enough, often down to the range of 10 - 15mA. Full discharge is a bit trickier to gauge, as the end-of-discharge (EoD) voltage will be reached before the battery is actually empty when discharging with high currents because of the internal resistance. So the EoD has to be reached at a low enough current for it to be a full discharge.

The fact that the battery will typically never get fully discharged because the host/application shuts down represents a challenge when trying to estimate the remaining charge and runtime to empty.

13 Battery characterization data

The Atmel SB202 needs a table for SoC versus OCV, a table for how much less capacity is available at higher currents, and, optionally, but recommended, the full charge capacity.

The SB200 can be used together with the PC demonstration software to log all data that is available from the SB202, and can, therefore, be used as a platform for characterizing batteries.

13.1 Full-charge capacity

The full-charge capacity of the battery is often different from the design capacity. The battery will update the full-charge capacity if it determines it is not correct.

The full-charge capacity as well as the design capacity should be the amount of capacity available at a very low current; that is, about 10mA.

This parameter is stored in the EEPROM in the battery_pack_parameters module.

13.2 State of charge vs. voltage

The voltage-based gas gauging uses a table of the OCV at different SoCs from 0% to 100%. The SB202 does a linear interpolation between the two closest points in the table, so the SoCs don't have to be at a fixed interval. This allows having fewer values between 70% and 30%, where the OCV is almost linear for most batteries, and more values near the end of the discharge, where the voltage changes a lot more.

NOTE The SB202 requires having values at exactly 100% and 0%.

The table is stored in the voltage_based_SoC module.

13.3 Remaining capacity compensation

Because of the internal battery resistance and the fact that it increases towards the end of a discharge, it is not possible to get as much capacity out of a battery at higher currents. Therefore the SB202 needs to know how much less capacity is available at different currents to know how much longer the battery can sustain the current load.

The SB202 supports an arbitrary number of currents in the remaining capacity compensation table and will interpolate between the two closest. If the current is higher than the highest value in the table, it will predict the compensation value by using the two highest values.

The internal resistance of the battery varies with the temperature, but this is not yet supported by this implementation.





14 Cell balancing

When using multi-cell battery packs, it is important that they are balanced with regard to cell voltage to get maximum capacity from the battery pack. To understand why, understanding the lithium-ion charge cycle is required:

The charger will charge with either the maximum charge current or the maximum charge voltage. In the beginning of the charge cycle, when the battery is almost empty, the charge current will reach the maximum limit. Hence, when the battery starts building a certain charge level, the charge voltage will increase and eventually reach the voltage limit (typically 4.2V per Li-ion cell), and thus be the limiting factor for the charger. An intelligent charger will not allow the charge voltage of the battery pack to increase above this level, and, as a result, the charge current will decrease. These two stages are called constant current charge and constant voltage charge.

The problem is that when using two cells, the charger will have the voltage limit at 8.4V. If one cell is more charged than the other, that is, in misbalance, it will reach the maximum charge voltage sooner than the other cell. In this case, the most charged cell could have reached 4.2V, while the least charged is at 4.1V. In this situation, the voltage of the battery stack is 8.3V and the charger will not notice that one of the battery cells has reached its maximum charge voltage. The charger will continue the constant current charge and the voltage will continue to increase until the battery pack voltage is 8.4V. This means that the most charged cell may reach 4.25V, which is the absolute maximum voltage for safety reasons, and the Atmel SB202 will disable the charge FET.

When this happens, neither cell is fully charged as a lithium-ion cell should be charged at maximum charge voltage for quite some time. If the problem arises, there is a high risk that the cell misbalance will continue to get worse and worse. As a result, if the cells are highly misbalanced, the charger will not be able to operate as intended and the battery pack will not be charged to its maximum capacity.

The solution used by the SB202 is to discharge the most charged cell until the voltage difference between the cells is low enough. The threshold, called ${\sf BATTPARAM_MISBALANCE_VOLTAGE_THRESHOLD, is stored in {\sf EEPROM} in the}$ battery pack parameters module.

As misbalancing is primarily an issue while charging a battery pack, cell balancing is active only while charging the battery. During discharging, activation of cell balancing would have limited effect. Be aware that if two highly misbalanced cells are operating together, it may take several charge-discharge cycles to balance the cells.

In the Atmel ATmega16HVB/32HVB, the balancing FETs are internal, and no external FETs are required. The filtering resistors limit the maximum balancing current that can flow through the internal FETs. It should be noted that as the balancing FETs are internal, the dissipated power will affect the temperature of the chip. Depending on the maximum balancing current, the internal temperature can be raised up to 30 degrees in room temperature. The cell balancing should, therefore, be disabled at a certain level if the external temperature NTC is not used to monitor the battery cell temperatures.

For 2s battery packs, the cell balancing algorithm is as simple as balancing the top most cell of the two cells. For 3s and 4s battery packs, the algorithm is more complex. The ATmega16HVB/32HVB can balance up to two cells at a time as long as they are not adjacent to each other. For example, cells one and three can be balanced at the same time, but not cells one and two. For a 3s and 4s implementation, the cell with

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the highest voltage will be balanced, and if the second highest cell voltage is not an adjacent cell, this will also be balanced.

The algorithm will not balance the third highest voltage cell if the second one is adjacent to the highest cell and can't be balanced. This would only make the lowest cells more unbalanced, and are, therefore, not balanced until they reach the voltage of the highest cells.

In addition, in order to increase the charging efficiency, the algorithm permits the cell balancing to take place only if the remaining state of charge is larger than 80%.





Figure 14-1. Flowchart of cell balancing for a four-cell application.



15 Power management

To save battery power, the Atmel ATmega16HVB/32HVB should sleep as much as possible in power-save mode. However, it should not enter power-save if a peripheral module that does not operate in power-save mode is being used. In this implementation, that means the VADC and the timers.

²⁴ AVR474

AVR474

The VADC might still be running at the end of the main loop if the main loop is executed faster than one VADC scan. In that case the ATmega16HVB/32HVB will enter ADC noise-reduction mode and wake up by the VADC interrupt when the conversion is finished.

The timers are used by the fast RC calibration and the communication. When they are used, the part can only enter idle mode. As the calibration is initiated from the firmware, it is always known when the calibration is running. It is, however, more difficult to determine if the communication is active, as this is caused by an external event.

A transmission is started by a start bit that triggers the external interrupt request. The interrupt routine then starts the timer to know when to sample the bits in the message. The challenge is that a start bit can be received after the check to determine if communication is active. The solution is to set sleep mode to idle in the external interrupt routine.

The ATmega16HVB/32HVB will enter power-off if one of the following conditions occurs:

- The chip temperature is outside the ATmega16HVB/32HVB limit (see Section 3.2.2)
- The battery voltage is very low (see Section 3.2.3)





16 Communication

The Atmel SB202 uses the SMBus interface to communicate with the host/application. The host has to initiate the communication, and the SB202 will communicate only if asked. On some errors, according to the SMBus specification, a timeout mechanism on the SCL line is used to detect the errors.

The command set is the SBS specification 1.1 from http://www.sbs-forum.org. The specification is not followed completely, some commands are not fully supported, and some reserved commands are used. See Chapter 17 for the list of commands.

16.1 SMBus interface (TWI)

The Atmel ATmega16HVB/32HVB has built-in, optimized TWI controller supporting SMBus implementation. The SB202 only has SMBus slave operation mode: slave transmitter mode and slave receiver mode.

The state changes are implemented in the TWI serial interrupt. From the SB202 side, one transaction starts from slave address matching, which can wake up the ATmega16HVB/32HVB from power-save mode. But for the following command and data transmission in the same transaction, the device must be kept in active mode or idle mode because the data arrival cannot awake devices from a sleep mode deeper than idle mode.

The SB202 accepts received messages with or without the packet error-checking code (PEC). When transmitting, the SB202 is always prepared to send the PEC after sending the message. If the host does not want a PEC, it can send a NACK signal after the last data byte to notify the SB202.

The communication speed is determined by the SMBus host. The speed can range from 10kHz to 100kHz.

16.2 Protocol

The SBS specification uses the SMBus protocol. The SB202 is compatible with SMBus specification 1.1. According the SBS specification, the battery pack address is fixed at 0x16.

The SB202 supports four different types of messages:

- Read word
- Write word
- Read block
- Write block

A word command always has two bytes of data, and a block command always has 32 bytes, which is different from the SBS block commands, which have variable lengths.

After the start signal, the host sends a byte (eight bits), including the seven mostsignificant bits, the slave address, and the LSB, the read/write flag (0 means write and 1 means read).

All the command codes are one byte, and are divided into word commands and block commands. Both sides should have to agree what every command is.

The SB202 firmware supports the PEC implementation. The PEC is a CRC8 with polynomial 0x8D (CRC8-CCITT) calculated from the command and all data bytes.

16.2.1 Read commands

On read commands, the host first writes the command to the Atmel SB202, and then restarts the communication with the read flag. After that, the slave places the data bytes on the SDA line one by one.

16.2.2 Write command

On write commands, the host sends the command byte and data bytes consecutively to the SB202. After SB202 receives one byte, it replies with a one-bit ACK or non-ACK signal. After the last data byte, the SB202 sends out an ACK signal to ask for a PEC byte from the host. But if the host does not support the PEC function, it will send a stop (P) signal, from which the slave can know the message is finished.





Figure 16-2. A write word command.



Figure 16-3. A read block command.



Figure 16-4. A write block command.



16.2.3 Errors

If errors occur during the communication, the SB202 can extend the clock low on the SCL line for more than 25ms. And after that, the SB202 can release the TWI line and reset the TWI controller. The errors include:

- Wrong command returned by the SB202
- Frame error on data sent from the SB202 •
- PEC incorrect on data sent from the SB202

16.3 Authentication

The SB202 contains both an AES encryption algorithm and a SHA256-based HMAC that can be used for challenge-response authentication. It allows the host to make sure the connected battery is a model it is compatible with.

Both algorithms cannot be used at the same time, and the decision must be made at compile time using two defines, AUTH USE AES and AUTH USE HMAC SHA2.





AES uses a 16-byte (128-bit) key, and a challenge and response size of 16 bytes. HMAC-SHA256 uses a 32-bytes (256-bit) key, and challenge and response size of 31 bytes. The use of AES and HMAC-SHA2 is identical except for the difference in challenge and response size.

Both the battery and the host have to know the key in advance. Typically, all batteries of the same model will have the same key preloaded, and the host may have a couple of keys to support different battery models.

The default key for HMAC-SHA256 is "This is a long key for HMAC-SHA2." The key preprogrammed into the SB202 at assembly for AES is "You cannot pass!" But a real application should not use a key consisting only of printable characters.

Both AES and HMAC-SHA256 are considered secure and are approved by, among others, the NSA. No known attack (other than brute-force) is known for either one (as of May 2008). Both algorithms run in constant time to avoid timing-based side-channel attacks. Nevertheless, the strength of the authentication also relies on other factors, which may be exploited in side-channel attacks, such as how the key is stored in the memory, how the challenge response is performed, and much more. If a very high security level is required, the application developer is encouraged to learn good cryptology practice and apply it.

From a pure brute-force perspective, the authentication methods used in this application note will be quite strong: On the AES 128-bit key, a brute-force attack would take, on average, 2^{127} (1.7*10³⁸) tries to find the right key. If someone wants to break the key in one year (32.6*10⁶ sec), and uses 1 million (10⁶) computers in parallel, it will demand that each computer can do:

 $\frac{Keys}{\sec \cdot computers} = \frac{1.7 \cdot 10^{38}}{32.6 \cdot 10^6 \cdot 10^6} = 5.2 \cdot 10^{24} \text{ key tries / sec}$

This is equal to approximately 5200 million-million complete AES encryptions of 16 bytes using a 128-bit key per nanosecond. So, even with a good portion of luck, one should not expect to identify the key within a fair amount of time based on brute force attacks. Still, it is left to the designer to ensure that the cryptographic method used is sufficiently strong for the desired purpose, and that it is used with best practices.

16.3.1 Authentication procedure

The host first has to ask what model the battery is to figure out which key to use. The next step is to send random data to the battery. The battery then executes the AES or HMAC-SHA256 algorithm on the data with the shared key. When the host reads the response from the battery, it can verify that the battery has used the correct key and can be quite sure it is the model it says it is.

The step-by-step procedure is as follows:

- 1. The host sends the authenticate command (an SBS write block command) to the battery. The first byte is always 0x01 in this implementation (it is used by the battery to know when a new challenge has arrived). After that, 16 bytes of random data should be sent for AES and 31 bytes for HMAC-SHA256.
- 2. The battery then runs the algorithm on the received data. Note that HMAC-SHA256 also includes the status byte (as the first byte in the data) in the calculations, so when verifying the response, the host also has to do that. It also means that the message length used when padding in the SHA256 algorithm should be calculated from a challenge length of 32 bytes.

- The host sends the authenticate command again to read the changed data, but this time as an SBS read block command. The first byte is a status byte, (described in Table 16-1) and the rest is the response. For HMAC-SHA256, the last byte of the response has to be truncated to fit in the 32-byte block message.
- 4. The host then verifies the data from the battery and checks that the algorithm was run with the correct key

Status byte	Description
0x01	Authentication has not started yet
0x02	Authentication has started, but not finished
0x04	Authentication is finished
0x08	An error occurred

Table 16-1. Read authentication status byte

16.3.2 Importance of random data

It is very important that the host does not send the same challenge for every authentication. If it does, a battery can hard-code the response and won't have to know the key, rendering the authentication useless for determining if a compatible battery is connected. The same issue applies if only a few different data combinations are used.

The best way to protect against this sort of attack is to send pseudo-random data concatenated with some unique data for each host/application. The unique data can, for example, be a serial number. Much more information about this can be found on the Internet and in books about cryptology. Search for "replay attack."





17 List of communication commands

17.1 SBS-compliant commands

The following commands are almost implemented as defined in the Smart Battery Data Specification Revision 1.1, available at http://www.sbs-forum.org. The Atmel SB202 does not support using and returning data in power (mW) instead of current (mA), so the commands that should support both only support current.

- ManufacturerAccess
- RemainingCapacityAlarm
- RemainingTimeAlarm
- AtRate
- AtRateToFull
- AtRateToEmpty
- AtRateOK
- Voltage
- Current
- AverageCurrent
- RelativeStateOfCharge
- AbsoluteStateOfCharge
- RemainingCapacity
- FullChargeCapacity
- RunTimeToEmpty
- AverageTimeToEmpty
- AverageTimeToFull
- ChargingCurrent
- ChargingVoltage
- CycleCount
- DesignCapacity
- DesignVoltage
- SpecificationInfo
- ManufacturerDate
- SerialNumber
- ManufacturerName
- DeviceName
- DeviceChemistry
- ManufacturerData

17.2 Non-SBS-compliant commands

Most of the following commands exist in the Smart Battery Data Specification, but they are implemented a bit differently in the SB202. Some new commands are also used, either with the optional SBS commands or reserved commands.

AVR474

Battery	/Mode	0x03
Read w	vord.	
The bits he SB2 Some r	s defined and described in SBS are used, but they are not set to their d 202 doesn't support the default settings) and changing them is not poss eserved bits are replaced with cell balancing information and FET statu	efault values (sible. ıs.
Bit	Description	
15	CAPACITY_MODE	
	Set to 0 – "Report in mA or mAh"	
14	CHARGER_MODE	
	Set to 1 – "Disable broadcasts of ChargingVoltage and ChargingCur SB202 cannot initiate communication	rrent" as the
13	ALARM_MODE	
	Set to 1 – "Disable AlarmWarning broadcast" as the SB202 cannot in communication	nitiate
12	BALANCING_CELL3	
	Set when cell 3 is being discharged to keep the cells balanced	
11	BALANCING_CELL2	
	Set when cell 2 is being discharged to keep the cells balanced	
10	BALANCING_CELL1 Set when cell 1 is being discharged to keep the cells balanced	
9	PRIMARY_BATTERY	
	Set to 0 – "Battery operating in its secondary role"	
8	CHARGE_CONTROLLER_ENABLED	
	Set to 0 – "Internal Charge Control Disabled"	
7	CONDITION_FLAG	
	Set to 0 – "Battery OK"	
6	BALANCING_CELL4	
	Set when cell 4 is being discharged to keep the cells balanced	
5	DUVRD from FCSR	
	Is set to the deep under-voltage recovery disabled bit from the FET status register	control and
4	CPS from FCSR	
	Set to the current protection status bit from the FET control and state	us register
3	DFE from FCSR	
	Set to the discharge FET enabled bit from the FET control and statu	s register
2	CFE from FCSR	
	Set to the charge FET enabled bit from the FET control and status r	egister
1	PRIMARY_BATTERY_SUPPORT	
	Set to 0 – Function not supported	
0	INTERMAL_CHARGE_CONTROLLER	
	Set to 0 – Function not supported	





Temperature

Read word

This should return the battery pack temperature. The SB202 will return the chip temperature in 0.1 Kelvin. TemperatureNTC1/TemperatureNTC2 can be used for getting the battery temperature

MaxError

This command is not supported

RemainingCapacity

Read word

According to the specification, this should return the remaining capacity at 0.2C discharge current. The SB202 will return the remaining capacity at the average current

Battery	/Status	0x16
Read w This co used ar	rord. mmand is basically implemented as specified in SBS, except that reserved b nd the error codes are not supported.	its are
Bit	Description	
15	OVER_CHARGED_ALARM	
	Controlled by the chargingProhibited flag	
14	TERMINATE_CHARGE_ALARM	
	Controlled by the voltageTooHigh flag	
13	VREGMON_TRIGGERED	
	Reserved bit in SBS, is set if the voltage regulator monitor triggered since time BatteryStatus was read. It is cleared when read	the last
12	OVER_TEMP_ALARM	
	Controlled by the cellTemperatureTooHigh flag	
11	TERMINATE_DISCHARGE_ALARM	
	Is set when remaining capacity is below a defined limit (SBS_TERMINATE_DISCHARGE_LIMIT) and cleared when a charge is of Recommended to use REMAINING_CAPACITY_ALARM instead, as it is configurable at runtime	letected.
10	BATTERY_PROTECTION_TRIGGERED	
	Set if the battery protection hardware module has disabled the FETs since time this command was read. Will be cleared when read	the last
9	REMAINING_CAPACITY_ALARM	
	Set if the remaining capacity is lower than the value set by the RemainingCapacityAlarm command. Updated once every minute	
8	REMAINING_TIME_ALARM	
	Set if AverageTimeToEmpty is less than the value set by the RemainingTi command. Updated once every minute	meAlarm
7	INITIALIZED	
	Controlled by be inverse of the criticalConditionDetected flag	
	Because both FETs will be disabled when that flag is set, the host/application	tion can

only detect that criticalConditionDetected is set if it also is connected to a charger

32

0x08

0x0C

0x0F

0x24

0x2A

0x2B

6	DISCHARGING Set if the current in the last second was a discharge
5	FULLY_CHARGED Set when the battery is considered fully charged and cleared as soon as a discharge current higher than standby is detected
4	FULLY_DISCHARGED Set when there is no capacity left in the battery at all. TERMINATE_DISCHARGE_ALARM and the remaining capacity/time alarm functions can be used to get earlier warnings. Is cleared when RelativeStateOfCharge is above 20%
3-0	Error Codes Not supported

Authentication

Read and write block Described in Section 16.3

ShuntCalibration

Read and write word

Non-SBS command. Is used to set the shunt resistor value in EEPROM. The value is set in micro-ohms and supports values between 4000 and $16000\mu\Omega$; however, no check is done on the value. Reading this command can be used to ensure the write command was successfully received

FETDisable

Write word

Non-SBS command. This command can be used to individually force the charge and discharge FETs to be disabled, which can be useful for demonstration and testing purposes. If bit 0 is high in the word, the charge FET will be disabled and kept disabled until this command is sent again with bit 0 low. Bit 1 works the same way for the discharge FET. Note that this command cannot force the FETs to be enabled; it can only force them to be disabled

StorageMode 0x2C Write word Non-SBS command. This command will force the ATmega16HVB/32HVB to enter power-off

mode. To make sure a power-off really is wanted, the word sent has to be 0xFADE, or this command will do nothing

TemperatureNTC2	0x2D
Read word	
Non-SBS command. If a second NTC is connected, this will return its temperature in	า 0.1
Kelvin. If no NTC is connected, 0 Kelvin is returned	





TemperatureNTC1

Read word

Non-SBS command. If the first NTC is connected, this will return its temperature in 0.1 Kelvin. If no NTC is connected, 0 Kelvin is returned

VoltageCell4

Read word

Returns the voltage over cell 4 in mV. If only three cells are used, it will return 0

VoltageCell3

Read word

Returns the voltage over cell 3 in mV. If only two cells are used, it will return 0

VoltageCell2

Read word

Returns the voltage over cell 2 in mV

VoltageCell1

Read word

Returns the voltage over cell 1 in mV

0x2E

0x3F

0x3D

0x3E

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